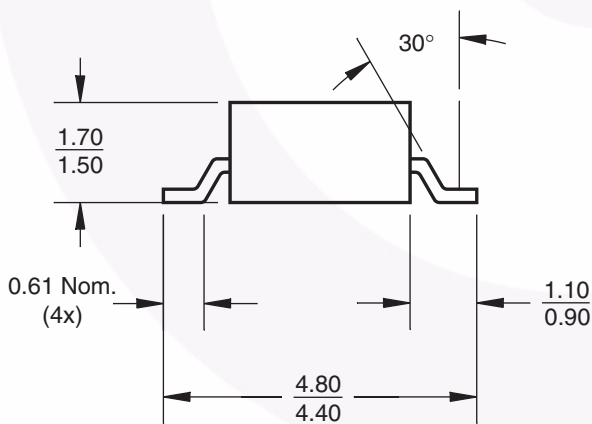
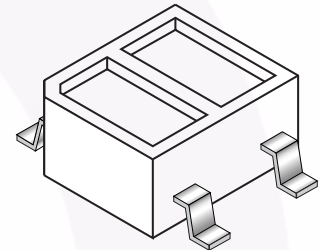
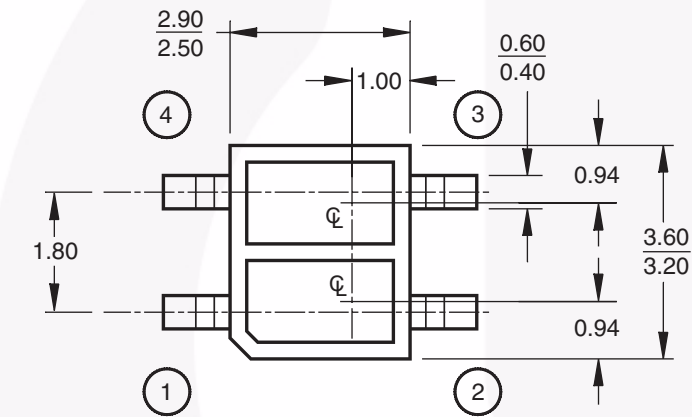


QRE1113GR SMT Reflective Object Sensor

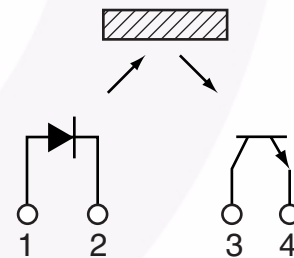
Features

- Phototransistor output
- Tape and reel packaging
- No contact surface sensing
- Miniature package
- Lead form style: Gull Wing

Package Dimensions



Schematic



PIN 1 ANODE PIN 3 COLLECTOR

PIN 2 CATHODE PIN 4 EMITTER

Notes:

1. Dimensions for all drawings are in millimeters.
2. Tolerance of ± 0.15 mm on all non-nominal dimensions

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Rating	Units
T_{OPR}	Operating Temperature	-25 to +85	$^\circ\text{C}$
T_{STG}	Storage Temperature	-30 to +90	$^\circ\text{C}$
T_{SOL-I}	Soldering Temperature (Iron) ^(2,3,4)	240 for 5 sec	$^\circ\text{C}$
T_{SOL-F}	Soldering Temperature (Flow) ^(2,3)	260 for 10 sec	$^\circ\text{C}$
EMITTER			
I_F	Continuous Forward Current	50	mA
V_R	Reverse Voltage	5	V
I_{FP}	Peak Forward Current ⁽⁵⁾	1	A
P_D	Power Dissipation ⁽¹⁾	75	mW
SENSOR			
V_{CEO}	Collector-Emitter Voltage	30	V
V_{ECO}	Emitter-Collector Voltage	5	V
I_C	Collector Current	20	mA
P_D	Power Dissipation ⁽¹⁾	50	mW

Electrical/Optical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
INPUT DIODE						
V_F	Forward Voltage	$I_F = 20\text{mA}$		1.2	1.6	V
I_R	Reverse Leakage Current	$V_R = 5\text{V}$			10	μA
λ_{PE}	Peak Emission Wavelength	$I_F = 20\text{mA}$		940	—	nm
OUTPUT TRANSISTOR						
I_D	Collector-Emitter Dark Current	$V_{CE} = 20\text{V}, I_F = 0\text{mA}$			100	nA
COUPLED						
$I_{C(ON)}$	On-State Collector Current	$I_F = 20\text{mA}, V_{CE} = 5\text{V}^{(6)}$	0.10	0.40		mA
$V_{CE(SAT)}$	Saturation Voltage				0.3	V
t_r	Rise Time	$V_{CC} = 5\text{V}, I_{C(ON)} = 100\mu\text{A}, R_L = 1\text{k}\Omega$		20		μs
t_f	Fall Time			20		

Notes:

- Derate power dissipation linearly 1.00mW/ $^\circ\text{C}$ above 25 $^\circ\text{C}$.
- RMA flux is recommended.
- Methanol or isopropyl alcohols are recommended as cleaning agents.
- Soldering iron 1/16" (1.6mm) from housing.
- Pulse conditions: $t_p = 100\mu\text{s}; T = 10\text{ms}$.
- Measured using an aluminum alloy mirror at $d = 1\text{mm}$.

Typical Performance Curves

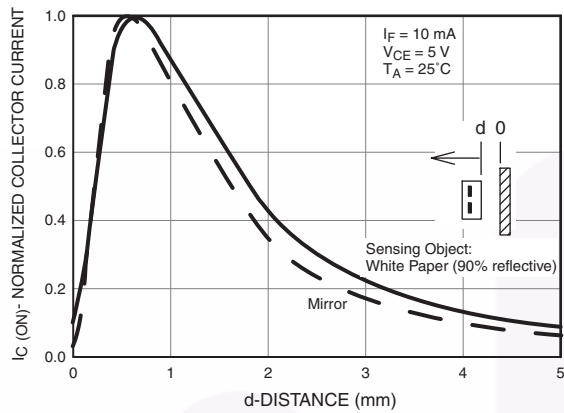


Fig. 1 Normalized Collector Current vs. Distance between device and reflector

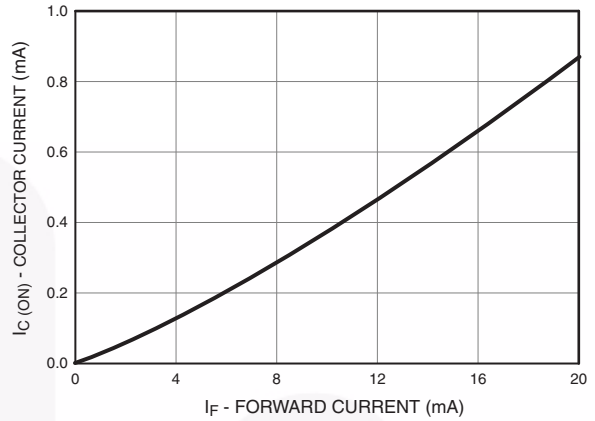


Fig. 2 Collector Current vs. Forward Current

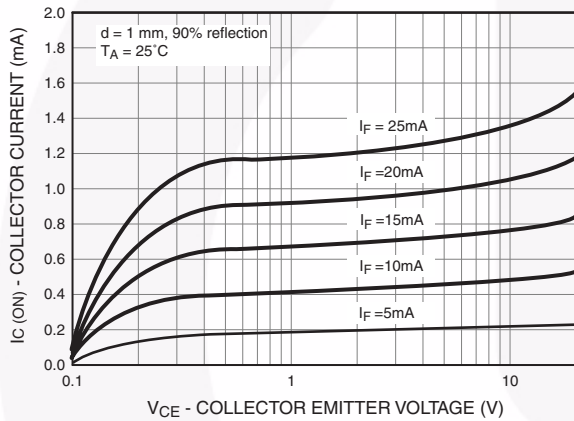


Fig. 3 Collector Current vs. Collector to Emitter Voltage

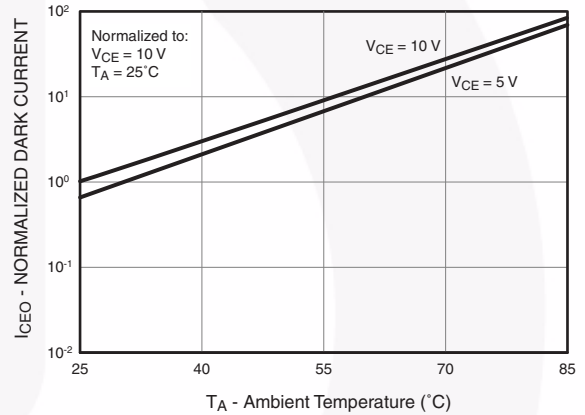


Fig. 4 Collector Emitter Dark Current (Normalized) vs. Ambient Temperature

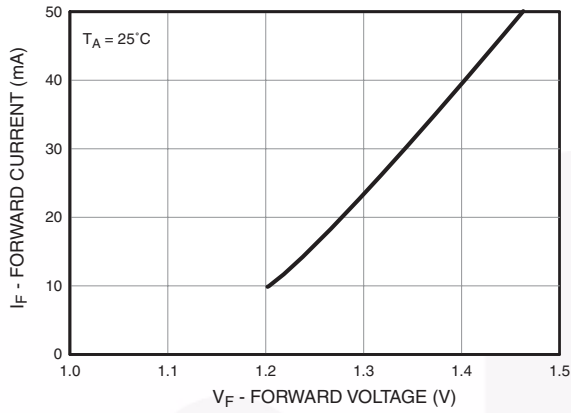


Fig. 6 Forward Current vs. Forward Voltage

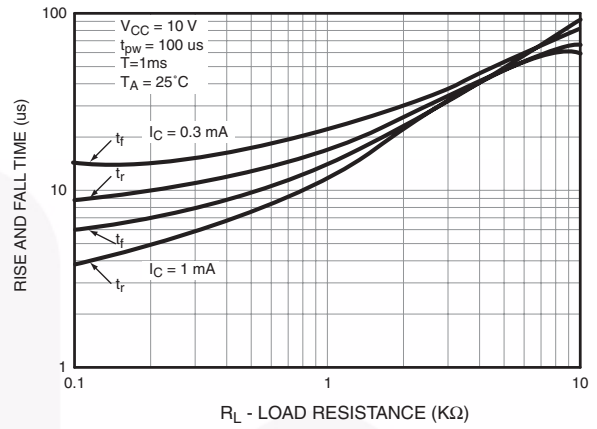


Fig. 7 Rise and Fall Time vs. Load Resistance

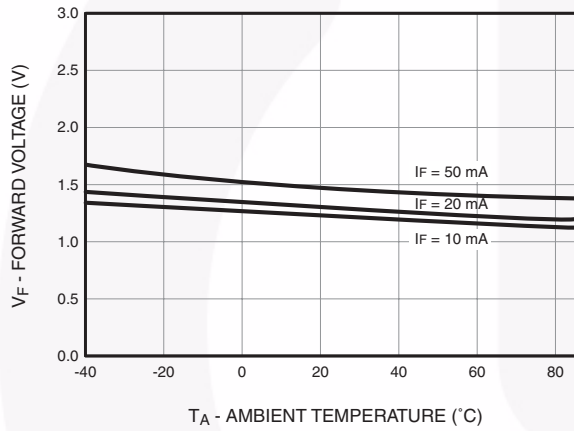


Fig. 8 Forward Voltage vs. Ambient Temperature

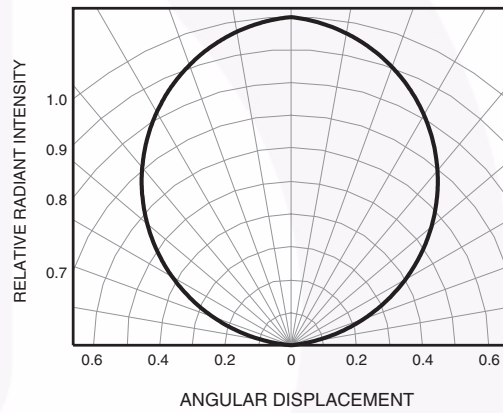
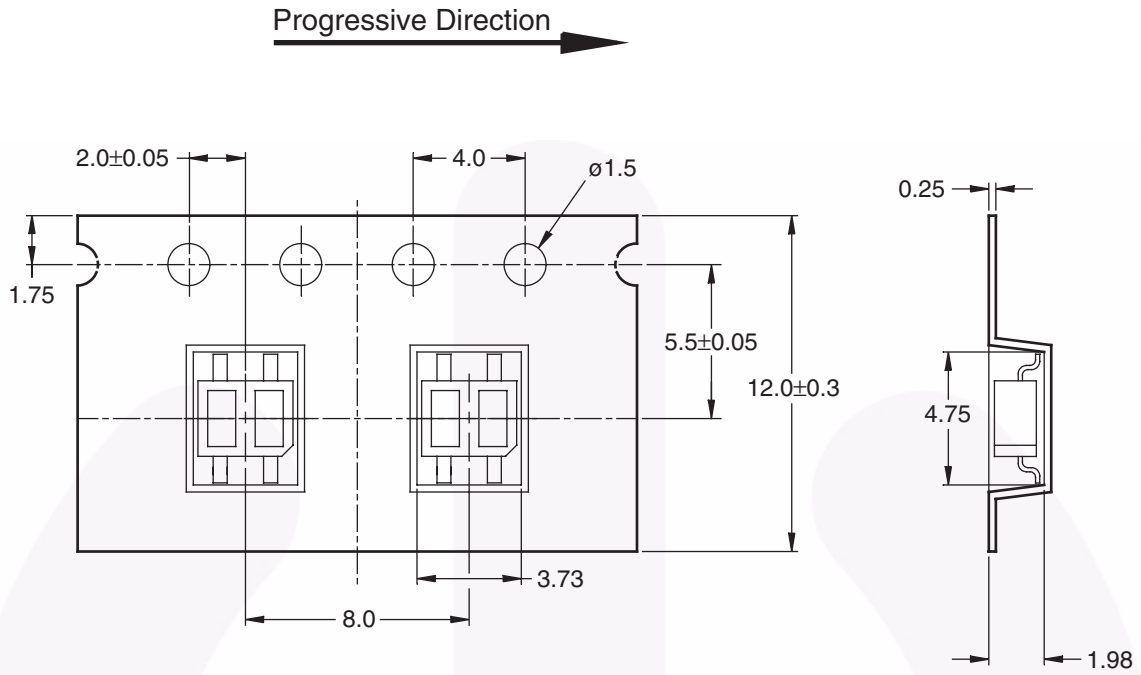


Fig. 8 Radiation Diagram

Taping Dimensions





General tolerance ±0.1
Dimensions in mm



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Rev. I32